# ne<mark>x</mark>peria

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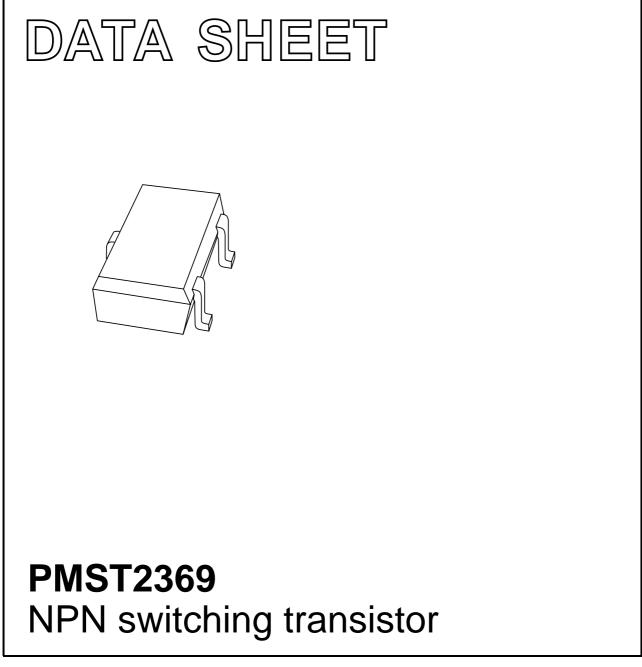
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 May 05 1999 Apr 22



#### Product data sheet

## NPN switching transistor

#### **FEATURES**

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

#### **APPLICATIONS**

• High-speed switching applications, primarily in portable and consumer equipment.

#### DESCRIPTION

NPN switching transistor in a SOT323 plastic package.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>		
PMST2369	*1J		

#### Note

- 1. \* = : Made in Hong Kong.
  - \* = t : Made in Malaysia.

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	15	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>C</sub>	collector current (DC)		-	200	mA
I <sub>CM</sub>	peak collector current	$t_p \le 10 \ \mu s$	-	300	mA
I <sub>BM</sub>	peak base current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C;$ note 1	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

PINNING

PIN

1

2

3

base

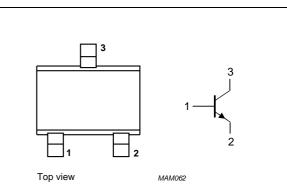
emitter

collector

#### Note

1999 Apr 22

1. Transistor mounted on an FR4 printed-circuit board.



DESCRIPTION

Fig.1 Simplified outline (SOT323) and symbol.

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## NPN switching transistor

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### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	625	K/W	

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

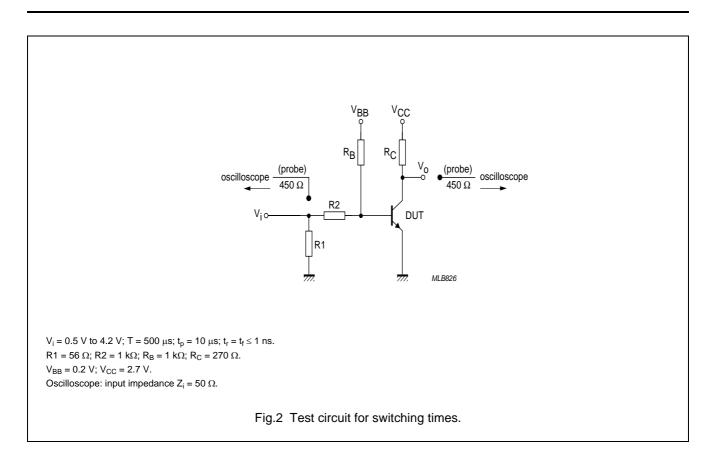
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V	_	400	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 20 V; T <sub>j</sub> = 125 °C	-	30	μA
I <sub>EBO</sub>	emitter cut-off current	$I_{C} = 0; V_{EB} = 4 V$	-	100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 1 V	40	120	
		$I_{C}$ = 10 mA; $V_{CE}$ = 1 V; $T_{amb}$ = -55 °C	20	-	
		I <sub>C</sub> = 100 mA; V <sub>CE</sub> = 2 V; note 1	20	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	-	250	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	700	850	mV
Cc	collector capacitance	$I_E = i_e = 0; V_{CB} = 5 V; f = 1 MHz$	-	4	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	500	-	MHz
Switching ti	mes (between 10% and 90% levels	s); (see Fig.2)			
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 3 mA;	_	10	ns
t <sub>d</sub>	delay time	I <sub>Boff</sub> = -1.5 mA	_	4	ns
t <sub>r</sub>	rise time		_	6	ns
t <sub>off</sub>	turn-off time		_	20	ns
ts	storage time		_	10	ns
t <sub>f</sub>	fall time		_	10	ns

#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

## NPN switching transistor

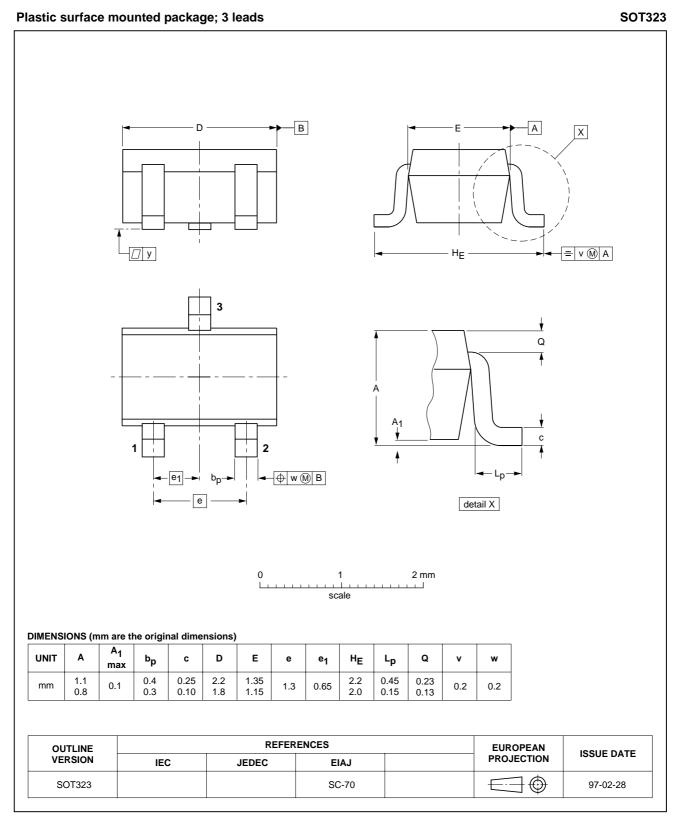
## **PMST2369**



**PMST2369** 

## NPN switching transistor

#### PACKAGE OUTLINE



## NPN switching transistor

**PMST2369** 

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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